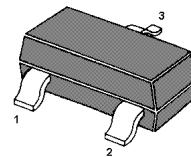


# MMBTSA1235

## PNP Silicon Epitaxial Planar Transistor

for low frequency amplification applications

The transistor is subdivided into two groups E and F, according to its DC current gain.



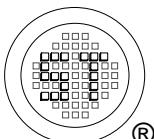
1. Base 2. Emitter 3. Collector  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	200	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

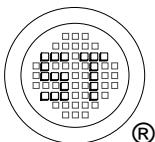
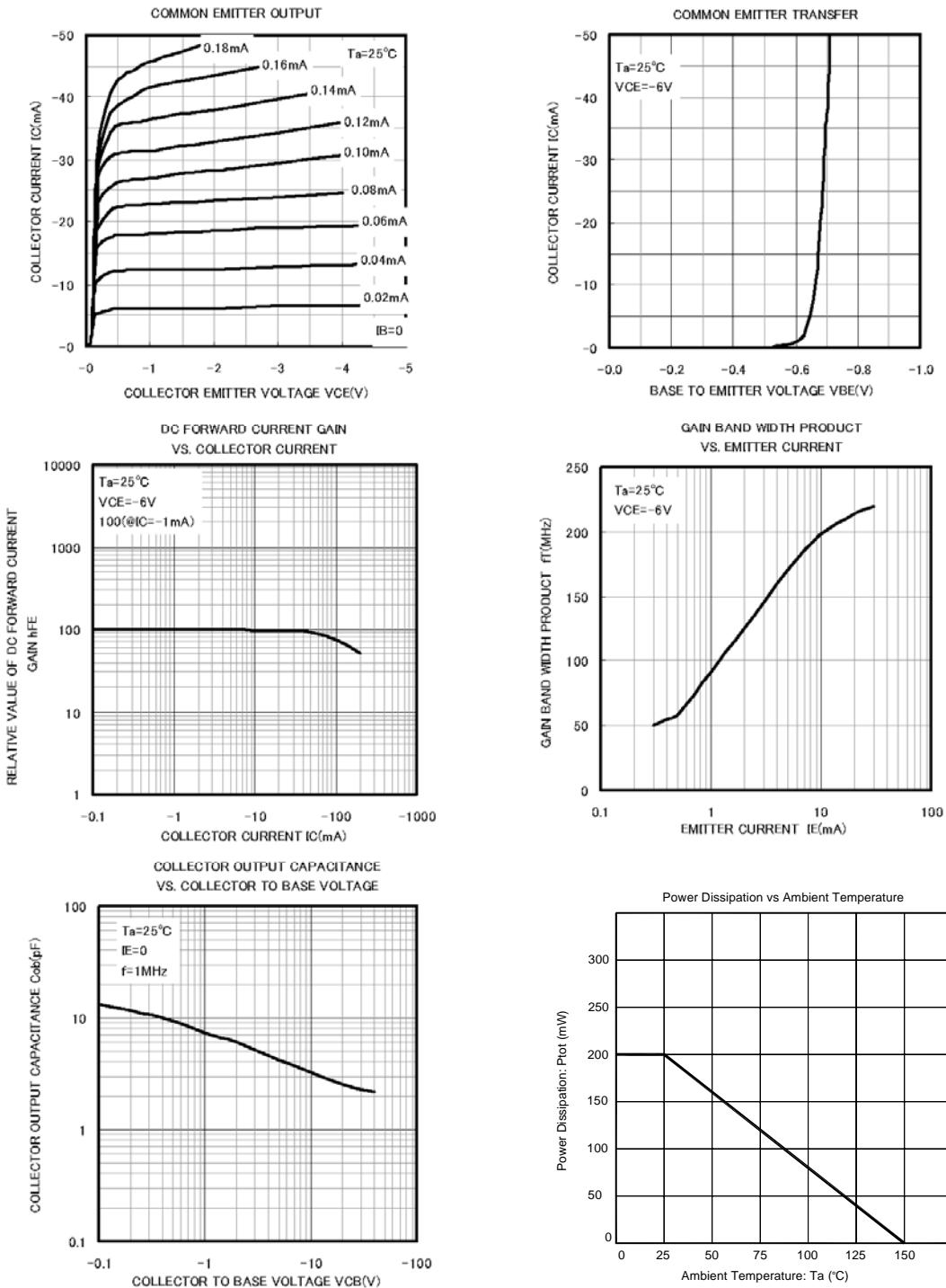
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 6 \text{ V}$ , $-I_C = 1 \text{ mA}$	$h_{FE}$	150	-	300	-
	$h_{FE}$	250	-	500	-
	$h_{FE}$	90	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 60 \text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 6 \text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100 \mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 100 \mu\text{A}$	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_C = 100 \mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 100 \text{ mA}$ , $-I_B = 10 \text{ mA}$	$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Saturation Voltage at $-I_C = 100 \text{ mA}$ , $-I_B = 10 \text{ mA}$	$-V_{BE(sat)}$	-	-	1	V
Gain Bandwidth Product at $-V_{CE} = 6 \text{ V}$ , $-I_C = 10 \text{ mA}$	$f_T$	-	200	-	MHz
Collector Output Capacitance at $-V_{CB} = 6 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{ob}$	-	4	-	pF



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